









SN65C3232E, SN75C3232E

SLLS697B - DECEMBER 2005 - REVISED JUNE 2021

SNx5C3232E 3-V To 5.5-V Two-Channel RS-232 1-MBIT/S Line Drivers and Receivers With ±15-kV IEC ESD Protection

1 Features

- Operate with 3-V to 5.5-V V_{CC} supply
- Operate up to 1 Mbit/s
- Low supply current . . . 300 µA typical
- External capacitors . . . $4 \times 0.1 \mu F$
- Accept 5-V logic input with 3.3-V supply
- Latch-up performance exceeds 100 mA Per JESD 78. class II
- ESD protection for RS-232 pins
 - ±15-kV Human-body model (HBM)
 - ±15-kV IEC 61000-4-2 Air-gap discharge
 - ±8-kV IEC 61000-4-2 Contact discharge

2 Applications

- **Industrial PCs**
- Wired networking
- Data center and enterprise computing
- Battery-powered systems
- **PDAs**
- **Notebooks**
- Palmtop PCs
- Hand-held equipment

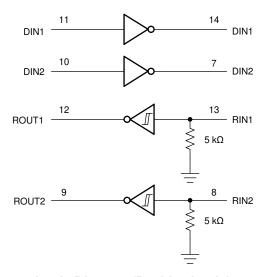
3 Description

The SN65C3232E and SN75C3232E consist of two line drivers, two line receivers, and a dual chargepump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). These devices provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 1 Mbit/s and a driver output slew rate of 14 V/µs to 150 V/µs.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)		
	D (SOIC)	9.90 mm x 3.91 mm		
SN65C3232E	DB (SSOP)	6.20 mm x 5.30 mm		
SN75C3232E	DW (SOIC)	10.3 mm x 7.50 mm		
	PW (TSSOP)	5.00 mm x 4.40 mm		

For all available packages, see the orderable addendum at the end of the data sheet.



Logic Diagram (Positive Logic)



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (December 2007) to Revision B (June 2021)

Page

- Added Device Information table, Pin Configuration and Functions section, Thermal Information tables, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section
 Updated the list of Applications
 Added a note specifying a minimum capacitor of 1 µF between V_{CC} and GND to satisfy IEC ESD specifications in the ESD Protection, Driver table



5 Pin Configuration and Functions

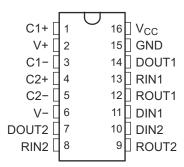


Figure 5-1. D, DB, DW, or PW Package (Top View)

Table 5-1. Pin Functions

F	PIN	I/O ⁽¹⁾	DESCRIPTION
NAME	D, DB, DW or PW	DESCRIPTION	
C1+	1	-	Positive lead of C1 capacitor
V+	2	0	Positive charge pump output for storage capacitor only
C1-	3	-	Negative lead of C1 capacitor
C2+	4	-	Positive lead of C2 capacitor
C2-	5	-	Negative lead of C2 capacitor
V-	6	0	Negative charge pump output for storage capacitor only
DOUT2	7	0	RS232 line data output (to remote RS232 system)
RIN2	8	1	RS232 line data input (from remote RS232 system)
ROUT2	9	0	Logic data output (to UART)
DIN2	10	I	Logic data input (from UART)
DIN1	11	I	Logic data input (from UART)
ROUT1	12	0	Logic data output (to UART)
RIN1	13	I	RS232 line data input (from remote RS232 system)
DOUT1	14	0	RS232 line data output (to remote RS232 system)
GRD	15	-	Ground
V _{CC}	16	-	Supply Voltage, Connect to external 3-V to 5.5-V power supply
Thermal Pad	-	-	Exposed thermal pad. Can be connected to GND or left floating.

⁽¹⁾ Signal Types: I = Input, O = Output, I/O = Input or Output.



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) see (1)

				MIN	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾			-0.3	6	V
V+	Positive output supply voltage range ⁽²⁾			-0.3	7	V
V-	Negative output supply voltage range ⁽²⁾			0.3	-7	V
V+ – V–	Supply voltage difference ⁽²⁾				13	V
V	Input voltage range	Drivers		-0.3	6	V
V _I		Receivers		-25	25	V
V	Output valtage range	Drivers		-13.2	13.2	V
Vo	Output voltage range Receivers			-0.3	V _{CC} + 0.3	V
TJ	Operating virtual junction temperature				150	°C
T _{stg}	Storage temperature range			-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute MaximumRatings do not imply functional operation of the device at these or any other conditions beyond those listed underRecommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime..

6.2 ESD Protection

			VALUE	UNIT	
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾ .	±3000	V	
V (ESD) Electi	Liectiostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	- V	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 ESD Protection, Driver

PIN		TEST CONDITIONS	TYP	UNIT
NAME	NO.	TEST CONDITIONS	116	UNII
		HBM, per ANSI/ESDA/JEDEC JS-001	±15	
DOUT	7, 14	IEC 61000-4-2 Air-Gap Discharge (1)	±15	kV
		IEC 61000-4-2 Contact Discharge (1)	±8	

⁽¹⁾ For D, DB, PW packages of SN65C3232E and PW package of SN75C3232E: A minimum of 1-μF capacitor is needed between VCC and GND to meet the specified IEC ESD level

6.4 ESD Protection, Receiver

P	PIN TEST CONDITIONS		TYP	UNIT
NAME	NO.	TEST CONDITIONS	111	UNII
		HBM, per ANSI/ESDA/JEDEC JS-001	±15	
RIN	8, 13	IEC 61000-4-2 Air-Gap Discharge (1)	±15	kV
		IEC 61000-4-2 Contact Discharge (1)	±8	

(1) For D, DB, PW packages of SN65C3232E and PW package of SN75C3232E: A minimum of 1-μF capacitor is needed between VCC and GND to meet the specified IEC ESD level

⁽²⁾ All voltages are with respect to network GND.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Recommended Operating Conditions

see note (1)

				MIN	NOM	MAX	UNIT
	Supply voltage		V _{CC} = 3.3 V	3	3.3	3.6	V
	Supply voltage		V _{CC} = 5 V	4.5	5	5.5	v
V _{IH}	Driver high-level input voltage	DIN	V _{CC} = 3.3 V	2			V
		DIN	V _{CC} = 5 V	2.4			
V _{IL}	Driver low-level input voltage		DIN			0.8	V
.,	Driver input voltage		DIN	0		5.5	V
VI	Receiver input voltage			-25		25	v
_	Operating free-air temperature		SN65C3232E	-40		85	· °C
T _A			SN75C3232E	0		70	

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V (see Figure 9-1).

6.6 Thermal Information, SN65C3232E

			SN65C3232E				
THERMAL METRIC(1)		PW (TSSOP)	D (SOIC)	DW (SOIC)	DB (SSOP)	UNIT	
		16 Pins	16 Pins	16 Pins	16 Pins		
R _{θJA}	Junction-to-ambient thermal resistance	108.0	85.9	57.0	103.1	°C/W	
R _{θJC(top)}	Junction-to-case (top) thermal resistance	39.0	43.1	33.5	49.2	°C/W	
R _{θJB}	Junction-to-board thermal resistance	54.4	44.5	37.1	54.8	°C/W	
Ψ ЈТ	Junction-to-top characterization parameter	3.3	10.1	7.5	12.0	°C/W	
Ψ _{ЈВ}	Junction-to-board characterization parameter	53.8	44.1	37.1	54.1	°C/W	
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	°C/W	

For more information about traditional and new thermal metrics, see the <u>Semiconductor and IC package thermal metrics</u> application report.

6.7 Thermal Information, SN75C3232E

			SN75	C3232E		
		PW (TSSOP)	D (SOIC)	DW (SOIC)	DB (SSOP)	UNIT
THERMAL METRIC ⁽¹⁾		16 PINS	16 PINS	16 PINS	16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	108.0	82.0	57.0	46.0	°C/W
R $_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	39.0	36.7	33.5	36.2	°C/W
R _{θJB}	Junction-to-board thermal resistance	54.4	33.6	37.1	43.8	°C/W
Ψ ЈТ	Junction-to-top characterization parameter	3.3	4.2	7.5	4.2	°C/W
Ψ ЈВ	Junction-to-board characterization parameter	53.8	33.3	37.1	42.9	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.



6.8 Electrical Characteristics, Power

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽²⁾		MIN	TYP ⁽¹⁾	MAX	UNIT
I _{CC}	Supply current	No load,	V _{CC} = 3.3 V or 5 V		0.3	1	mA

⁽¹⁾ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

6.9 Electrical Characteristics, Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITI	MIN	TYP ⁽¹⁾	MAX	UNIT	
V _{OH}	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = GND	5	5.5		V
V _{OL}	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = V _{CC}	-5	-5.4		V
I _{IH}	High-level input current	V _I = V _{CC}			±0.01	±1	μΑ
I _{IL}	Low-level input current	V _I at GND			±0.01	±1	μA
Ios	Short-circuit output current	V _{CC} = 3.6 V,	V _O = 0 V		±35	±60	mA
l _{OS} (2)	Short-circuit output current	V _{CC} = 5.5 V,	V _O = 0 V		±35	±90	
r _o	Output resistance	V _{CC} , V+, and V- = 0 V,	V _O = ±2 V	300	10M		Ω

⁽¹⁾ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

6.10 Electrical Characteristics, Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS(2)	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{OH}	High-level output voltage	I _{OH} = -1 mA	V _{CC} - 0.6	V _{CC} - 0.1		V
V _{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	V
V _{IT+}	Positive-going input threshold voltage	V _{CC} = 3.3 V		1.5	2.4	V
VIT+	Positive-going input tilleshold voltage	V _{CC} = 5 V		1.8	2.4	v
V	Negative-going input threshold voltage	V _{CC} = 3.3 V	0.6	1.2		V
V _{IT}	Negative-going input tilleshold voltage	V _{CC} = 5 V	0.8	1.5		V
V _{hys}	Input hysteresis (V _{IT+} – V _{IT-})			0.3		V
r _i	Input resistance	$V_1 = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

⁽¹⁾ All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

⁽²⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 9-1).

⁽²⁾ Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

⁽³⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 9-1) .

⁽²⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 $V \pm 0.3$ V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 $V \pm 0.5$ V (see Figure 9-1).



6.11 Switching Characteristics, Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TE	MIN	TYP ⁽¹⁾ MAX	UNIT	
	Maximum data rate	$R_L = 3 k\Omega$,	$C_L = 250 \text{ pF}, \qquad V_{CC} = 3 \text{ V to } 4.5 \text{ V}$	1000		kbit/s
	(see Figure 7-1)	One DOUT switching	$C_L = 1000 \text{ pF}, \qquad V_{CC} = 3.5 \text{ V to } 5.5 \text{ V}$	1000	KDIUS	
t _{sk(p)}	Pulse skew ⁽²⁾	C_L = 150 pF to 2500 pF, R_L	= 3 k Ω to 7 k Ω , See Figure 7-2		300	ns
SR(tr)	Slew rate, transition region (see Figure 7-1)	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega, C_L = 150$) pF to 1000 pF, V _{CC} = 3.3 V	14	150	V/µs

- All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
- (2)
- Pulse skew is defined as $|t_{PLH} t_{PHL}|$ of each channel of the same device. Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 9-1).

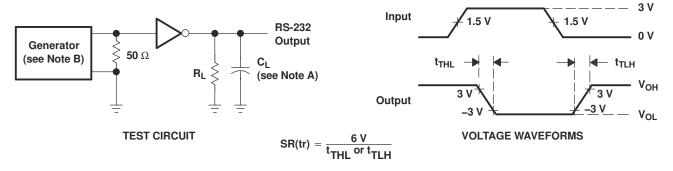
6.12 Switching Characteristics, Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS(3)	TYP ⁽¹⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C ₁ = 150 pF	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	CL = 130 pr	300	ns
t _{sk(p)}	Pulse skew ⁽²⁾		300	ns

- All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. (1)
- Pulse skew is defined as $|t_{PLH} t_{PHL}|$ of each channel of the same device. Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V ± 0.5 V (see Figure 9-1).

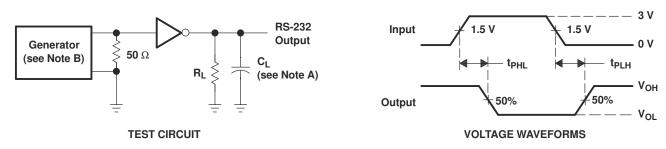
7 Parameter Measurement Information



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

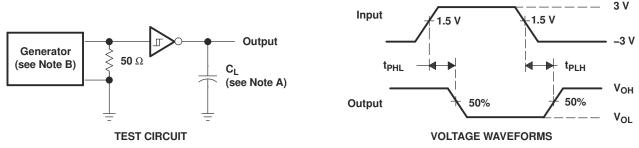
Figure 7-1. Driver Slew Rate



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 7-2. Driver Pulse Skew



NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $Z_O = 50 \ \Omega$, 50% duty cycle, $t_r \le 10 \ ns$, $t_f \le 10 \ ns$.

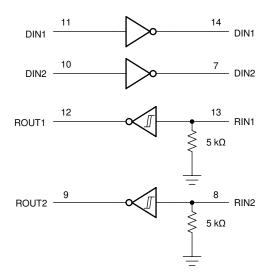
Figure 7-3. Receiver Propagation Delay Times

8 Detailed Description

8.1 Overview

The SNx5C3232E device consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV IEC ESD protection between serial-port connection terminals and GND. The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from one 3-V to 5.5-V supply. The device operates at data signaling rates up to 1 Mbps and a maximum of 150-V/µs driver output slew rate. Outputs are protected against shorts to ground.

8.1.1 Functional Block Diagram



8.1.2 Feature Description

8.1.2.1 Power

The power block increases, inverts, and regulates voltage at V+ and V- pins using a charge pump that requires four external capacitors.

8.1.2.2 RS232 Driver

Two drivers interface the standard logic level to RS232 levels. Both DIN inputs must be valid high or low.

8.1.2.3 RS232 Receiver

Two receivers interface RS232 levels to standard logic levels. An open input results in a high output on ROUT. Each RIN input includes an internal standard RS232 load.



8.1.3 Device Functional Modes

Table 8-1. Each Driver

INPUT DIN ⁽¹⁾	OUTPUT DOUT
L	Н
Н	L

(1) H = high level, L = low level

Table 8-2. Each Receiver

INPUT RIN ⁽¹⁾	OUTPUT ROUT					
L	Н					
Н	L					
Open	Н					

(1) H = high level, L = low level, Open = input disconnected or connected driver off

8.1.3.1 V_{CC} Powered by 3 V to 5.5 V

The device is in normal operation.

8.1.3.2 V_{CC} Unpowered, $V_{CC} = 0 V$

When the SNx5C3232E device is unpowered, it can be safely connected to an active remote RS232 device.

9 Application and Implenentation

Note

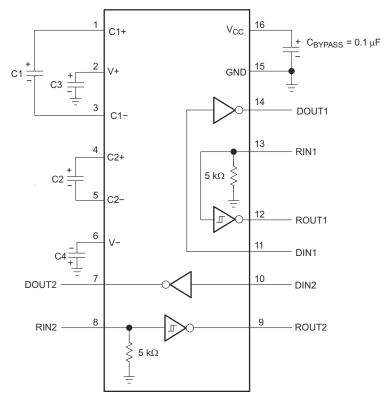
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SNx5C3232E device is designed to convert single-ended signals into RS232-compatible signals, and vice-versa. This device can be used in any application where an RS232 line driver or receiver is required.

ROUT and DIN connect to UART or general-purpose logic lines. RIN and DOUT lines connect to a RS232 connector or cable.

Typical Application



A. C3 can be connected to V_{CC} or GND.

Figure 9-1. Typical Operating Circuit and Capacitor Values

Table 9-1. V_{CC} vs Capacitor Values

V _{CC}	C1	C2, C3, C4							
3.3 V ± 0.3 V	0.1 μF	0.1 μF							
5 V ± 0.5 V	0.047 µF	0.33 μF							
3 V to 5.5 V	0.1 μF	0.47 μF							

9.2.1 Design Requirements

- Recommended V_{CC} is 3.3 V or 5 V
 - 3 V to 5.5 V is also possible
- Maximum recommended bit rate is 1 Mbps

9.2.2 Detailed Design Procedure

All DIN inputs must be connected to valid low or high logic levels. Select capacitor values based on V_{CC} level for best performance.

9.2.3 Application Performance Plots

VCC must be between 3 V and 5.5 V. Charge pump capacitors must be chosen using V_{CC} vs Capacitor Values

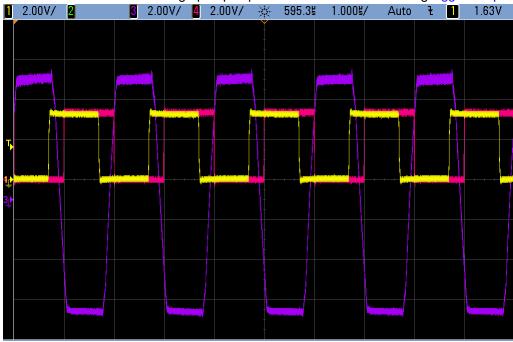


Figure 9-2. 1 Mbps timing waveform from driver input to receiver output loopback. DOUT to RIN trace is in purple, DIN trace is in yellow and ROUT trace is in pink



10 Power Supply Recommendations

The supply voltage, V_{CC} , should be between 3 V and 5.5 V. Select the charge-pump capacitors using V_{CC} vs Capacitor Values.

11 Layout

11.1 Layout Guidelines

Keep the external capacitor traces short, specifically on the C1 and C2 nodes that have the fastest rise and fall times.

11.2 Layout Example

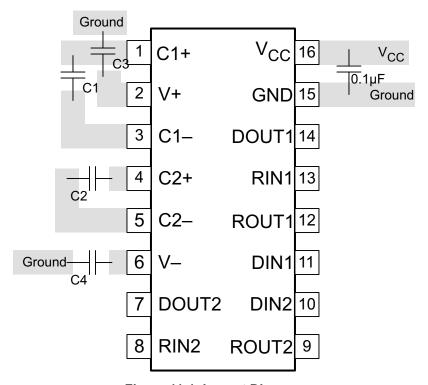


Figure 11-1. Layout Diagram

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN65C3232EDBR	ACTIVE	SSOP	DB	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EDBRG4	ACTIVE	SSOP	DB	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EDR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDRG4	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDW	LIFEBUY	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	
SN65C3232EDWR	LIFEBUY	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	
SN65C3232EPWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN75C3232EDW	LIFEBUY	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232E	
SN75C3232EDWR	LIFEBUY	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232E	
SN75C3232EPWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	MY232E	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

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(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3232EDBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN65C3232EDBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN65C3232EDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65C3232EDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65C3232EDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN65C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN75C3232EDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN75C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN75C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1



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*All dimensions are nominal

All difficultions are norminal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3232EDBR	SSOP	DB	16	2000	356.0	356.0	35.0
SN65C3232EDBR	SSOP	DB	16	2000	356.0	356.0	35.0
SN65C3232EDR	SOIC	D	16	2500	356.0	356.0	35.0
SN65C3232EDR	SOIC	D	16	2500	356.0	356.0	35.0
SN65C3232EDWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN65C3232EPWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN75C3232EDWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN75C3232EPWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN75C3232EPWR	TSSOP	PW	16	2000	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

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TUBE

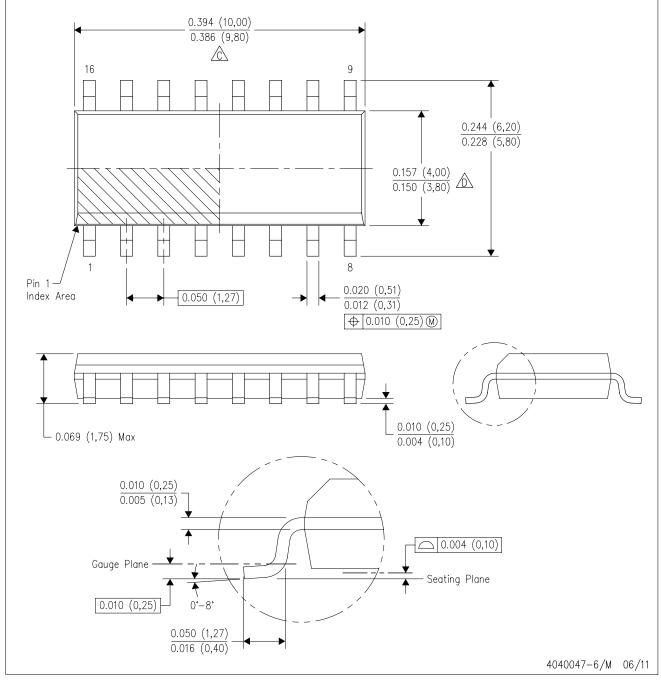


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65C3232EDW	DW	SOIC	16	40	506.98	12.7	4826	6.6
SN75C3232EDW	DW	SOIC	16	40	506.98	12.7	4826	6.6

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE

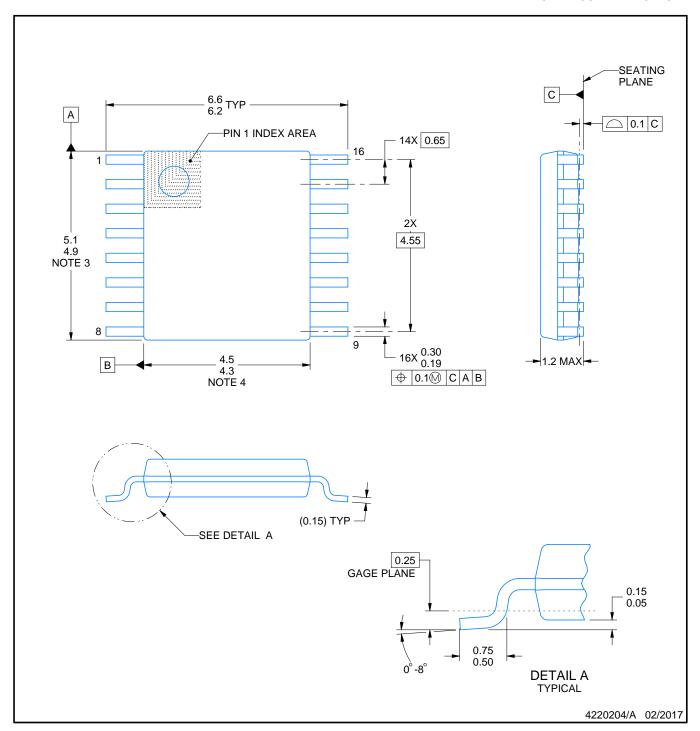


NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



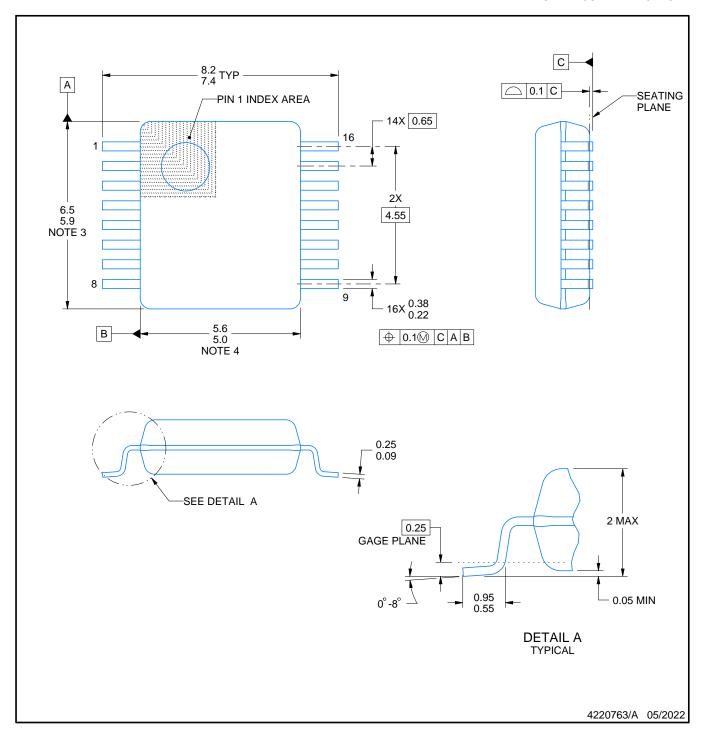


NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







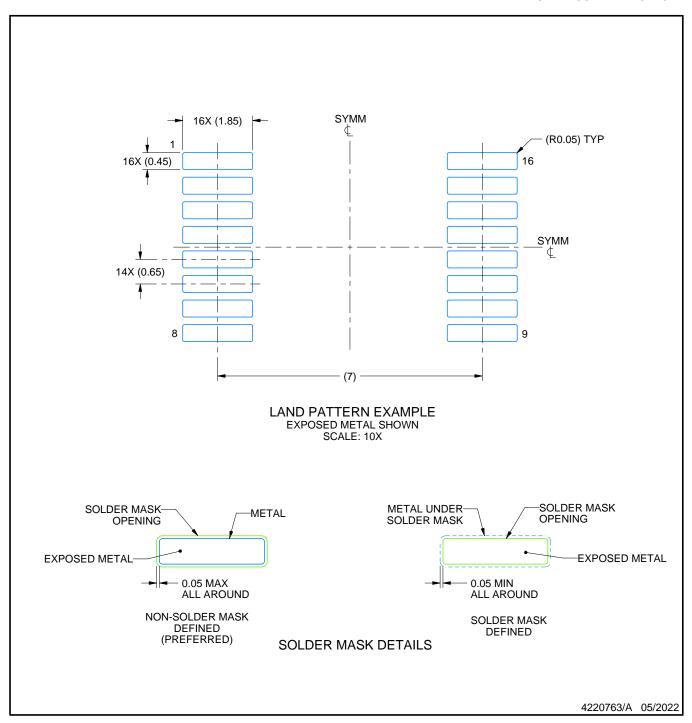
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-150.

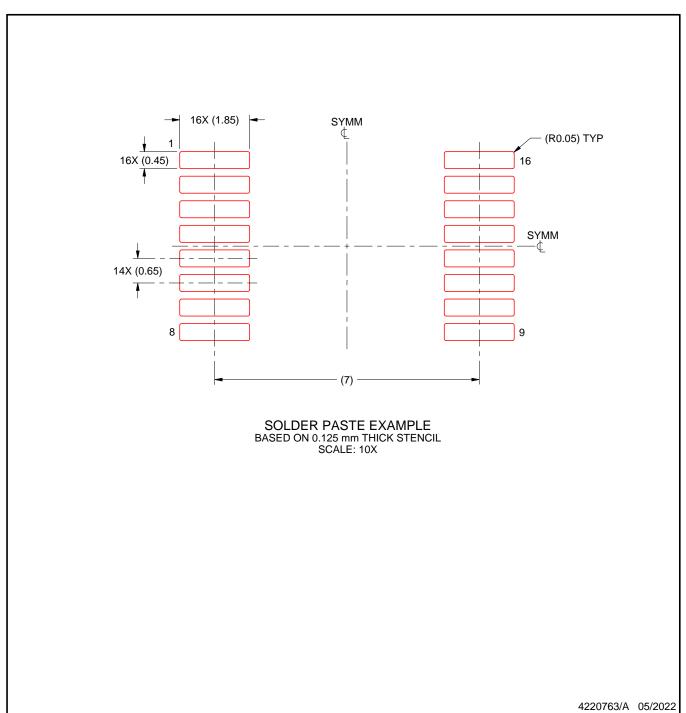




NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

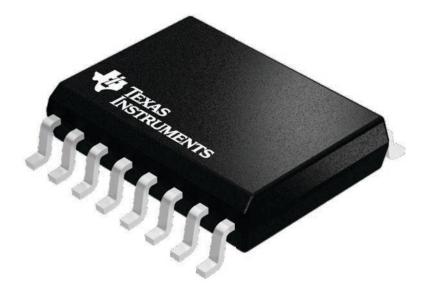
- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



7.5 x 10.3, 1.27 mm pitch

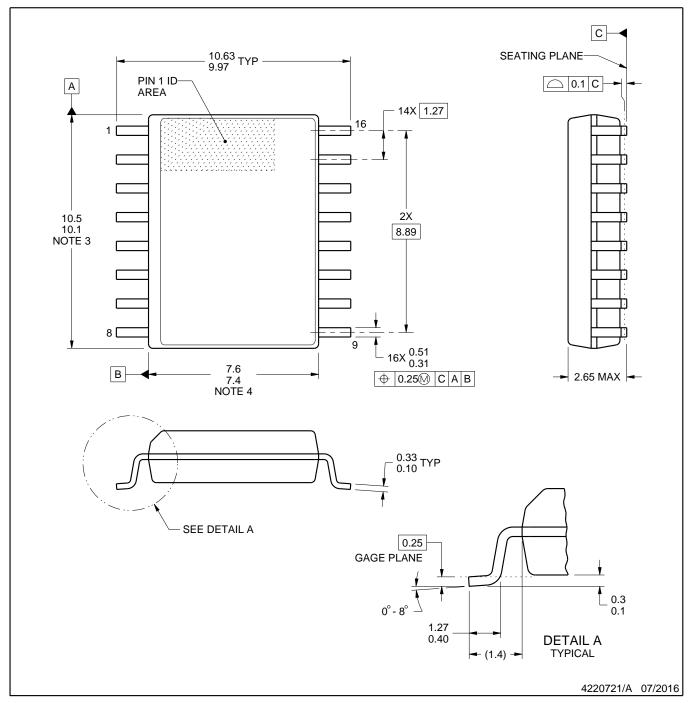
SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





SOIC



NOTES:

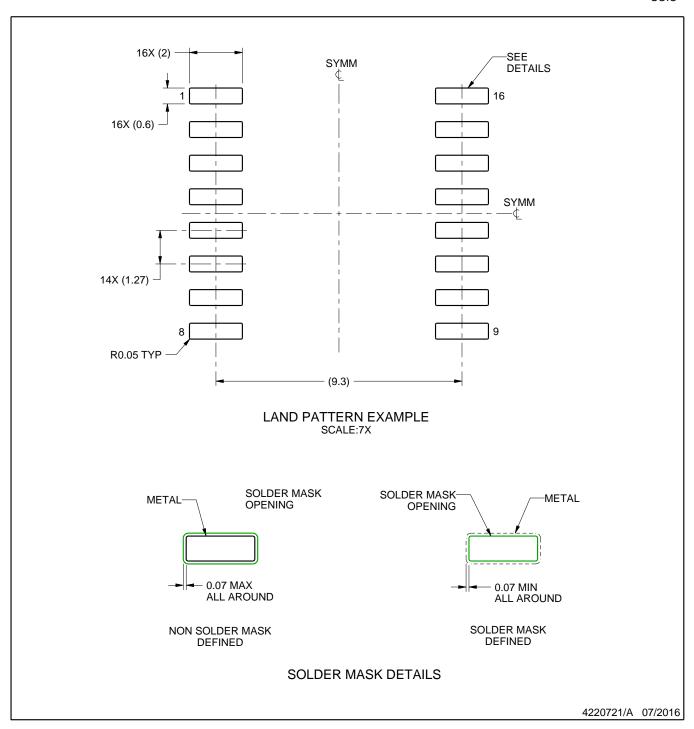
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



SOIC

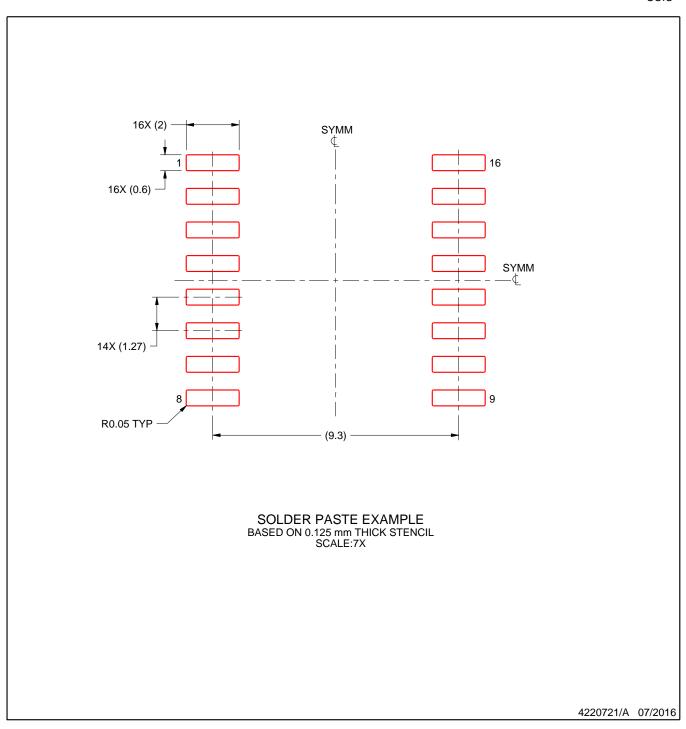


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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